L Numb r	Hits	S ar h Text	DB	Time stamp
165	2710	substrate same (insulating r di lectri ) and (type r onductivity) same (impurity r n ntrati n) sam l ctr de same junction	USPAT; US-PGPUB; EPO; JP ; DERWENT; IBM_TDB	2004/06/10 12:02
166	849	substrate same (insulating or dielectric) and (type or conductivity) same (impurity or concentration) same (higher or lower) same electrode same junction	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:02
167	707	substrate same (insulating or dielectric) and (type or conductivity) same (impurity or concentration) same (higher or lower) same electrode same junction same (film or layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:02
168	41	(substrate same (insulating or dielectric) and (type or conductivity) same (impurity or concentration) same (higher or lower) same electrode same junction same (film or layer)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:03
169	35	(substrate same (insulating or dielectric) same (type or conductivity) same (impurity or concentration) same (higher or lower) same electrode same junction same (film or layer)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:03
170	32	(substrate same (insulating or dielectric) same (type or conductivity) same (impurity or concentration) same (higher or lower) same electrode same junction same (film or layer) same (first or second or third or fourth or upper or lower or top or bottom)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:04
171	13	(substrate same (insulating or dielectric) same (type or conductivity) same (impurity or concentration) same (higher or lower) same electrode same junction same (film or layer) same (first or second or third or fourth or upper or lower or top or bottom) same (third or fouth).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:05
172	13	(substrate same (insulating or dielectric) same (type or conductivity) same (impurity or concentration) same (higher or lower) same electrode same junction same (film or layer) same (first or second or third or fourth or upper or lower or top or bottom) sam (third or fourth)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:05

173	9	(substrate same (insulating or diel tric) sam (type or c nductivity) same (impurity or con entration) same (higher or lower) am lectr d same juncti n sam (film r layer) same (first or second r third r fourth r upp r r l wer r top r b ttom) same (third or fourth)) and (control near electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:06
174	8	(substrate same (insulating or dielectric) same (type or conductivity) same (impurity or concentration) same (higher or lower) same electrode same junction same (film or layer) same (first or second or third or fourth or upper or lower or top or bottom) same (third or fourth)) and (control near electrode).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:06
175	2	(substrate same (insulating or dielectric) same (type or conductivity) same (impurity or concentration) same (higher or lower) same (control adj electrode) same junction same (film or layer) same (first or second or third or fourth or upper or lower or top or bottom) same (third or fourth)) and (control near electrode).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:08
176	2	((substrate same (insulating or dielectric) same (type or conductivity) same (impurity or concentration) same (higher or lower) same (control adj electrode) same junction same (film or layer) same (first or second or third or fourth or upper or lower or top or bottom) same (third or fourth)) and (control near electrode).clm.) and (concentration near2 higher).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:09
177	2	((substrate same (insulating or dielectric) same (type or conductivity) same (impurity or concentration) same (higher or lower) same (control adj electrode) same junction same (film or layer) same (first or second or third or fourth or upper or lower or top or bottom) same (third or fourth)) and (control near electrode).clm.) and (conductivity).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:09
178	0	(control adj electrode) and (first near conductivity near type) and (second near conducitivity near type)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:11
179	0	(c ntr l adj electr de) and (first near c ndu tivity near type) and (sec nd n ar conduitivity n ar typ )	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/10 12:11

180	1333	(control adj el ctrode) and (first near	USPAT;	2004/06/10
		conductivity n ar typ ) and (second n ar	US-PGPUB;	12:11
		ondu tivity n ar typ )	EP ; JPO;	*
			DERWENT;	
			IBM_TDB	
181	137	(c ntrol adj electrode) and (first n ar	USPAT;	2004/06/10
		conductivity near type) and (second near	US-PGPUB;	12:12
		conductivity near type) and ((third or fourth)	EPO; JPO;	
		near2 layer) and ((insulation or insulator or	DERWENT;	
		dielectric) near2 (layer or film))	IBM_TDB	
182	58	(control adj electrode) and (first near	USPAT;	2004/06/10
		conductivity near type) and (second near	US-PGPUB;	12:13
		conductivity near type) and ((third or fourth)	EPO; JPO;	
		near2 layer) and ((insulation or insulator or	DERWENT;	
		dielectric) near2 (layer or film)) and ((first	IBM_TDB	
		or second or third or fourth) near2	_	
		concentration)		
183	27	(control adj electrode).clm. and ((first or	USPAT;	2004/06/10
		scond or third) near conductivity).clm. and	US-PGPUB;	12:15
		((third or fourth) near2 layer) and	EPO; JPO;	
		((insulation or insulator or dielectric) near2	DERWENT;	
		(layer or film)) and ((first or second or third	IBM_TDB	
		or fourth) near2 concentration).clm.		
184	96	(control adj electrode).clm. and ((first or	USPAT;	2004/06/10
		scond or third) near conductivity).clm. and	US-PGPUB;	12:23
		((insulation or insulator or dielectric or	EPO; JPO;	12.20
		insulating) near2 (layer or film)).clm. and	DERWENT;	
		((first or second or third or fourth) near2	IBM_TDB	
		concentration).clm.	<del>-</del>	
185	53	(control adj electrode).clm. and ((first or	USPAT;	2004/06/10
		scond or third) near conductivity).clm. and	US-PGPUB;	12:19
		((insulation or insulator or dielectric or	EPO; JPO;	
		insulating) near2 (layer or film)).clm. and	DERWENT;	
		((first or second or third or fourth) near2	IBM_TDB	
		concentration).clm. and ((third or fourth)		
		near2 layer).clm.		
186	26	(control adj electrode).clm. and ((first or	USPAT;	2004/06/10
		scond or third) near conductivity).clm. and	US-PGPUB;	12:34
		((insulation or insulator or dielectric or	EPO; JPO;	
		insulating) near2 (layer or film)).clm. and	DERWENT;	
		((first or second or third or fourth) near2	IBM_TDB	
		concentration).clm. and junction.clm.	<u>-</u>	
187	11	(control adj electrode).clm. and ((first or	USPAT;	2004/06/10
		scond or third) near conductivity).clm. and	US-PGPUB;	12:35
		((insulation or insulator or dielectric or	EPO; JPO;	
		insulating) near2 (layer or film)).clm. and	DERWENT;	
		((first or second or third or fourth) near2	IBM_TDB	
		c ncentrati n).clm. and (junction same		
		(contr l adj el ctr de)).clm.		

400			NOT 3	0004/00/40
188	7	(contr   adj   le trode).clm. and ((first or	USPAT;	2004/06/10
		s ond r third) near conductivity).clm. and	US-PGPUB;	12:37
		((in ulati n rinsulat r rdi lectric r	EP ; JPO;	
		insulating) near2 (lay r r film)). lm. and	DERWENT;	
		((first r second r third r fourth) near2	IBM_TDB	
		conc ntration). Im. and (juncti n n ar10		
400		(control adj electrode)).clm.		0004/00/40
189	6	(control adj electrode).clm. and ((first or	USPAT;	2004/06/10
		scond or third) near conductivity).clm. and	US-PGPUB;	12:37
		((insulation or insulator or dielectric or	EPO; JPO;	
		insulating) near2 (layer or film)).clm. and	DERWENT;	
		((first or second or third or fourth) near2	IBM_TDB	
		concentration).clm. and (junction near10		
		(control adj electrode)).clm. and		
190		(concentration near3 (higher or lower)).clm.	HCDAT.	2004/06/40
190	6	(control adj electrode).clm. and ((first or	USPAT;	2004/06/10
		scond or third) near conductivity).clm. and	US-PGPUB;	12:38
		((insulation or insulator or dielectric or	EPO; JPO;	
		insulating) near2 (layer or film)).clm. and	DERWENT;	
		((first or second or third or fourth) near2	IBM_TDB	
		concentration).clm. and (junction near10		
		(control adj electrode)).clm. and		
191	97	(concentration near2 (higher or lower)).clm. (first near conductivity near type) and	HEDAT.	2004/06/10
131	31	(second near conductivity near type) and	USPAT; US-PGPUB;	12:39
		(fourth near2 (region or layer or portion))	EPO; JPO;	12:35
		and (control adj electrode) and junction and	DERWENT;	
		((impurity adj concentration) near (higher or	IBM_TDB	
		lower))	16111_166	
192	63	(first near conductivity near type) and	USPAT;	2004/06/10
		(second near conductivity near type) and	US-PGPUB;	12:41
		(fourth near2 (region)) and (control adj	EPO; JPO;	121-71
		electrode) and junction and ((impurity adj	DERWENT;	
		concentration) near (higher or lower))	IBM_TDB	
193	6	(first near conductivity near type) and	USPAT;	2004/06/10
		(second near conductivity near type) and	US-PGPUB;	12:42
		(fourth near2 (region)) and (control adj	EPO; JPO;	<del></del>
		electrode) and junction and ((impurity adj	DERWENT;	
		concentration) near (higher or lower)) and	IBM_TDB	
		(junction near5 conductivity)		
194	15	(first near conductivity near type) and	USPAT;	2004/06/10
		(second near conductivity near type) and	US-PGPUB;	12:42
		(fourth near2 (region)) and (control adj	EPO; JPO;	
		electrode) and junction and ((impurity adj	DERWENT;	
	İ	concentration) near (higher or lower)) and	IBM_TDB	
		(junction near10 conductivity)		
195	0	(first near conductivity near type) and	USPAT;	2004/06/10
		(second n ar conductivity near typ ) and	US-P PUB;	12:43
		(f urth n ar2 (regi n)) and ( ntrol adj	EPO; JPO;	
		el trode) and juncti n and ((impurity adj	DERWENT;	
		concentrati n) n ar (high r r lower)) and	IBM_TDB	
		(juncti n n ar10 c nductivity near10		
		( ontrol adj le tr d ))		

196	63	(first n ar conductivity n ar type) and	USPAT;	2004/06/10
		(second n ar onductivity n ar type) and	US-PGPUB;	12:43
1		(f urth n ar2 (region)) and (contr l adj	EP ; JPO;	
		lectr d ) and junction and ((impurity adj	DERWENT;	
		concentration) near (higher r l wer)) and junction	IBM_TDB	
197	29	(first near conductivity near type) and	USPAT;	2004/06/10
		(second near conductivity near type) and	US-PGPUB;	12:44
		(fourth near2 (region)) and (control adj	EPO; JPO;	
		electrode) and junction and ((impurity adj	DERWENT:	
		concentration) near (higher or lower)) and	IBM_TDB	
		junction.ti,ab,clm.		
198	5	(first near conductivity near type) and	USPAT;	2004/06/10
		(second near conductivity near type) and	US-PGPUB;	12:46
		(fourth near2 (region)) and (control adj	EPO; JPO;	
		electrode) and junction and ((impurity adj	DERWENT;	
		concentration) near (higher or lower)) and	IBM_TDB	
		(junction same conductivity same (control		•
		adj electrode)).ti,ab,clm.		
199	3	(first near conductivity near type) and	USPAT;	2004/06/10
		(second near conductivity near type) and	US-PGPUB;	12:47
		(fourth near2 (region)) and (control adj	EPO; JPO;	
		electrode) and junction and ((impurity adj	DERWENT;	
		concentration) near (higher or lower)) and	IBM_TDB	
		(junction same conductivity same (control		
		adj electrode) same ((insulating or		
		insulation or dielectric) near2 (layer or		
		film))).ti,ab,clm.		
200	0	(first near conductivity near type) and	USPAT;	2004/06/10
		(second near conductivity near type) and	US-PGPUB;	12:47
		(fourth near2 (region)) and (control adj	EPO; JPO;	
		electrode) and junction and ((impurity adj	DERWENT;	
		concentration) near (higher or lower)) and	IBM_TDB	
		(junction same conductivity same (control		
		adj electrode) same ((insulating or		
		insulation or dielectric) near2 (layer or		
		film))).ti,ab,clm. and capacitance		